Journal of Crystal Growth 84 (1987) 688–692
North-Holland, Amsterdam

AUTHOR INDEX

Airaksinen, V.M., T.S. Cheng and C.R. Stanley, Some kinetic and thermodynamic aspects of dopant incorporation in MBE grown InP and GaAs 84 (1987) 241
Alfaro, E.J., see García-Ruiz 84 (1987) 555
Amornkitbamrung, V. and S. Chatraphorn, Cubic Sn from liquid phase epitaxy on InSb 84 (1987) 326
Andersen, E., see Elwell 84 (1987) 335
Anderson, E.E., see Reiss 84 (1987) 7
Antson, H., see Tammenmaa 84 (1987) 151
Arber, J.M., P. Norman, D.S. Urch and D. Bloor, Crystals for soft X-ray spectroscopy 84 (1987) 145
Arends, J., J. Christoffersen, M.R. Christoffersen, H. Eckert, B.O. Fowler, J.C. Heughebaert, G.H. Nancollas, J.P. Yesinowski and S.J. Zawacki, A calcium hydroxyapatite precipitated from an aqueous solution; an international multi-method analysis 84 (1987) 515
Asplund, M., see Tammenmaa 84 (1987) 151
Atherton, L.J., J.J. Derby and R.A. Brown, Radiative heat exchange in Czochralski crystal growth 84 (1987) 57

Bartels, I., see Tolksdorf 84 (1987) 323
Bauer, G., see Clemens 84 (1987) 571
Berglund, K.A., see Cerreta 84 (1987) 577
Bertran, E., M. Varela, A. Lousa and J.L. Morenza, Crystalline properties of In-doped CdS thin films 84 (1987) 483
Beruto, D., see Giordani 84 (1987) 679
Birnbaum, H.K., see Stock 84 (1987) 419
Blaauw, C. and C.J. Miner, A gas mixing device for MOCVD 84 (1987) 191
Blaauw, C., B. Emmerstorfer and A.J. SpringThorpe, Cadmium doping of InP grown by MOCVD 84 (1987) 431
Block, J.H., see Melmed 84 (1987) 123
Bloor, D., see Arber 84 (1987) 145
Borh, H., C.S. Jacobsen, K.F. Nielsen, I. Johannsen and F. Kragh, Growth behaviour of the superconducting phase in Y–Ba–Cu–O systems 84 (1987) 332
Boisvert, R.F., see McFadden 84 (1987) 371
Bordui, P.F., J.C. Jacco, G.M. Loiacono, R.A. Stolzenberger and J.J. Zola, Growth of large single crystals of $KTiOPO_4$ (KTP) from high-temperature solution using heat pipe based furnace system 84 (1987) 403
Boulogne, B., see Doukhan 84 (1987) 167
Bredikhin, V.I., V.P. Ershov, V.V. Korolikhin, V.N. Lizyakina, S.Yu. Potapenko and N.V. Khlyunev, Mass transfer processes in KDP crystal growth from solutions 84 (1987) 509
Brown, R.A., see Atherton 84 (1987) 57
Bryndzia, L.T., see Heider 84 (1987) 50
Buchan, N.I. and F. Rosenberger, Mass spectroscopic characterization of the GeSe: GeI_4 vapor transport system 84 (1987) 359
Büttner, U., see Haspeklo 84 (1987) 196

Cerreta, M.K. and K.A. Berglund, The structure of aqueous solutions of some dihydrogen orthophosphates by laser Raman spectroscopy 84 (1987) 577
Chang, C.C., C.C. Wei, Y.K. Su and H.C. Tzeng, Growth and characterization of ZnSe single crystals by closed tube method 84 (1987) 11
Chatraphorn, S., see Amornkitbamrung 84 (1987) 326
Chen, H., see Stock 84 (1987) 419
Chen, W.C., M.Y. Ma, D.D. Liu and A.Y. Xie, The influence of pH on the habit and the rate of α-$LiIO_3$ crystal growth 84 (1987) 303
Chen, T.S., see Airaksinen 84 (1987) 241
Cheng, V.K.W. and B.A.W. Coller, Monte Carlo simulation study on the dissolution of a train of infinitely straight steps and of an infinitely straight crystal edge 84 (1987) 436
Chernov, A.A. and L.N. Rashkovich, Spiral crystal growth with nonlinear dependence of step growth rate on supersaturation; the {110} faces of KH_2PO_4 crystals in aqueous solution 84 (1987) 389
Clark III, W.W., see Neurgaonkar 84 (1987) 629
Clemens, H., P. Ofner, H. Krenn and G. Bauer, Epitaxial growth of $Pb_{1-x}Ge_xTe$ films and of $PbTe/Pb_{1-x}Ge_xTe$ superlattices 84 (1987) 571
Cockayne, B., see Wright 84 (1987) 552
Coller, B.A.W., see Cheng 84 (1987) 436
Cordier, P., see Doukhan 84 (1987) 167
Coriell, S.R., see McFadden 84 (1987) 371
Cory, W.K., see Neurgaonkar 84 (1987) 629
Christoffersen, J., see Arends 84 (1987) 515
Christoffersen, M.R., see Arends 84 (1987) 515

Journal of Crystal Growth 84 (1987) 688–692
North-Holland, Amsterdam

AUTHOR INDEX

Airaksinen, V.M., T.S. Cheng and C.R. Stanley, Some kinetic and thermodynamic aspects of dopant incorporation in MBE grown InP and GaAs 84 (1987) 241
Alfaro, E.J., see García-Ruiz 84 (1987) 555
Amornkitbamrung, V. and S. Chatraphorn, Cubic Sn from liquid phase epitaxy on InSb 84 (1987) 326
Andersen, E., see Elwell 84 (1987) 335
Anderson, E.E., see Reiss 84 (1987) 7
Antson, H., see Tammenmaa 84 (1987) 151
Arber, J.M., P. Norman, D.S. Urch and D. Bloor, Crystals for soft X-ray spectroscopy 84 (1987) 145
Arends, J., J. Christoffersen, M.R. Christoffersen, H. Eckert, B.O. Fowler, J.C. Heughebaert, G.H. Nancollas, J.P. Yesinowski and S.J. Zawacki, A calcium hydroxyapatite precipitated from an aqueous solution; an international multi-method analysis 84 (1987) 515
Asplund, M., see Tammenmaa 84 (1987) 151
Atherton, L.J., J.J. Derby and R.A. Brown, Radiative heat exchange in Czochralski crystal growth 84 (1987) 57

Bartels, I., see Tolksdorf 84 (1987) 323
Bauer, G., see Clemens 84 (1987) 571
Berglund, K.A., see Cerreta 84 (1987) 577
Bertran, E., M. Varela, A. Lousa and J.L. Morenza, Crystalline properties of In-doped CdS thin films 84 (1987) 483
Beruto, D., see Giordani 84 (1987) 679
Birnbaum, H.K., see Stock 84 (1987) 419
Blaauw, C. and C.J. Miner, A gas mixing device for MOCVD 84 (1987) 191
Blaauw, C., B. Emmerstorfer and A.J. SpringThorpe, Cadmium doping of InP grown by MOCVD 84 (1987) 431
Block, J.H., see Melmed 84 (1987) 123
Bloor, D., see Arber 84 (1987) 145
Borh, H., C.S. Jacobsen, K.F. Nielsen, I. Johannsen and F. Kragh, Growth behaviour of the superconducting phase in Y–Ba–Cu–O systems 84 (1987) 332
Boisvert, R.F., see McFadden 84 (1987) 371
Bordui, P.F., J.C. Jacco, G.M. Loiacono, R.A. Stolzenberger and J.J. Zola, Growth of large single crystals of $KTiOPO_4$ (KTP) from high-temperature solution using heat pipe based furnace system 84 (1987) 403
Boulogne, B., see Doukhan 84 (1987) 167
Bredikhin, V.I., V.P. Ershov, V.V. Korolikhin, V.N. Lizyakina, S.Yu. Potapenko and N.V. Khlyunev, Mass transfer processes in KDP crystal growth from solutions 84 (1987) 509
Brown, R.A., see Atherton 84 (1987) 57
Bryndzia, L.T., see Heider 84 (1987) 50
Buchan, N.I. and F. Rosenberger, Mass spectroscopic characterization of the GeSe: GeI_4 vapor transport system 84 (1987) 359
Büttner, U., see Haspeklo 84 (1987) 196

Cerreta, M.K. and K.A. Berglund, The structure of aqueous solutions of some dihydrogen orthophosphates by laser Raman spectroscopy 84 (1987) 577
Chang, C.C., C.C. Wei, Y.K. Su and H.C. Tzeng, Growth and characterization of ZnSe single crystals by closed tube method 84 (1987) 11
Chatraphorn, S., see Amornkitbamrung 84 (1987) 326
Chen, H., see Stock 84 (1987) 419
Chen, W.C., M.Y. Ma, D.D. Liu and A.Y. Xie, The influence of pH on the habit and the rate of α-$LiIO_3$ crystal growth 84 (1987) 303
Chen, T.S., see Airaksinen 84 (1987) 241
Cheng, V.K.W. and B.A.W. Coller, Monte Carlo simulation study on the dissolution of a train of infinitely straight steps and of an infinitely straight crystal edge 84 (1987) 436
Chernov, A.A. and L.N. Rashkovich, Spiral crystal growth with nonlinear dependence of step growth rate on supersaturation; the {110} faces of KH_2PO_4 crystals in aqueous solution 84 (1987) 389
Clark III, W.W., see Neurgaonkar 84 (1987) 629
Clemens, H., P. Ofner, H. Krenn and G. Bauer, Epitaxial growth of $Pb_{1-x}Ge_xTe$ films and of $PbTe/Pb_{1-x}Ge_xTe$ superlattices 84 (1987) 571
Cockayne, B., see Wright 84 (1987) 552
Coller, B.A.W., see Cheng 84 (1987) 436
Cordier, P., see Doukhan 84 (1987) 167
Coriell, S.R., see McFadden 84 (1987) 371
Cory, W.K., see Neurgaonkar 84 (1987) 629
Christoffersen, J., see Arends 84 (1987) 515
Christoffersen, M.R., see Arends 84 (1987) 515

Damman, H., see Tolksdorf 84 (1987) 323
Das, I., R.S. Lall and A. Pushkarna, Multiple stability and pH dependence on periodic precipitation in illuminated lead chromate system 84 (1987) 231
Derby, J.J., see Atherton 84 (1987) 57
Dixon, S., see Pickering 84 (1987) 180
Dodelet, J.-P., see Lawrence 84 (1987) 133
Donnelly, V.M., see McCracy 84 (1987) 253
Doukhan, J.C., B. Boulogne, P. Cordier, E. Philippot, J.C. Jumas and Y. Toudic, A transmission electron microscope study of lattice defects and water precipitation in α-berlinite $AlPO_4$ 84 (1987) 167
Du, Nguyen, see Lawrence 84 (1987) 133
Dutt, B.V., Constitutional supercooling in thin-melt multi-slice liquid phase epitaxy of undoped InGaAs/InP alloy structures 84 (1987) 163

Eckert, H., see Arends 84 (1987) 515
Eguchi, M., see Fujii 84 (1987) 237
Elwell, D. and E. Andersen, Modes of oscillation in melts from Fourier analysis of temperature–time data 84 (1987) 335
Emmerstorfer, B., see Blaauw 84 (1987) 431
Endo, T., see Sugiyama 84 (1987) 673
Ershov, V.P., see Bredikhin 84 (1987) 509

Fonstad, C.G., see Whitney 84 (1987) 676
Fornari, R., C. Paorici, L. Zanotti and L. Zecchina, Effect of crystal orientation on dislocation formation in LEC GaAs 84 (1987) 266
Fowler, B.O., see Arends 84 (1987) 515
Frank, O., see Melmed 84 (1987) 123
Fujii, T., M. Eguchi, T. Inada and T. Fukuda, Effects of crucible material on undoped LEC GaAs crystals 84 (1987) 237
Fujii, T., see Nakajima 84 (1987) 295
Fukuda, T., see Fujii 84 (1987) 237
Fukuda, T., see Kimura 84 (1987) 394

Gołacki, Z., K. Godwod, J. Majewski and G. Jasiołek, Precipitates in PbTe:Cr crystal grown by the Bridgman method 84 (1987) 455
Gasson, D.B., see Pickering 84 (1987) 180
García-Ruiz, J.M., A. Santos and E.J. Alfaro, Oscillatory growth rates in single crystals growing under diffusional control 84 (1987) 555
Gevelber, M.A. and G. Stephanopoulos, Dynamics and control of the Czochralski process. I. Modelling and dynamic characterization 84 (1987) 647
Ghaisas, S.V., see Thomsen 84 (1987) 79
Giordani, M. and D. Beruto, Effect of vaporization rate on calcium carbonate nucleation from calcium hydrogen carbonate aqueous solutions 84 (1987) 679
Gits-Léon, S., F. Lefaucheux and M.C. Robert, Mass transport by diffusion in a tetramethoxysilane gel 84 (1987) 155
Godwod, K., see Gołacki 84 (1987) 455
Goldenfeld, N., Theory of spherulitic crystallization 84 (1987) 601
Gombia, E., R. Panizzieri, G. Salviati and J. Vidal, Growth and characterization of sintered polycrystalline silicon 84 (1987) 621
Greene, P.D. and S.A. Wheeler, Electroabsorptive $In_{1-x}Ga_xAs_yP_{1-y}$ superlattices grown by liquid phase epitaxy 84 (1987) 259
Gualtieri, D.M., Liquid phase epitaxial growth of $Y_3(Al, Sc)_2Al_3O_{12}$ on (111)-oriented $Y_3Al_5O_{12}$ substrates 84 (1987) 399

Harries, J.E., D.W.L. Hukins, C. Holt and S.S. Hasnain, Conversion of amorphous calcium phosphate into hydroxyapatite investigated by EXAFS spectroscopy 84 (1987) 563
Hartmann, H., R. Mach and N. Testova, Vapour phase epitaxy of wide gap II–VI compounds 84 (1987) 199
Hashimoto, T., N. Ishizawa, N. Mizutani and M. Kato, Crystal growth and characterization of $La_{1-x}M_xMnO_3$ (M = Ca, Sr) 84 (1987) 207
Hasiguti, R.R., see Yumoto 84 (1987) 185
Hasnain, S.S., see Harries 84 (1987) 563
Haspeklo, H., U. Büttner, E. Sasse and U. König, Compositional homogeneity of MOVPE-grown InGaAs: dependence on reactor wall temperature and working pressure 84 (1987) 196
Heider, F. and L.T. Bryndzia, Hydrothermal growth of magnetite crystals (1 μm to 1 mm) 84 (1987) 50
Heughebaert, J.C., see Arends 84 (1987) 515
Heyraud, J.C. and J.J. Métois, Equilibrium shape of an ionic crystal in equilibrium with its vapour (NaCl) 84 (1987) 503
Hicks, T.W., Fluid motion in the encapsulant region of the LEC growth system 84 (1987) 598
Hiltunen, L., see Tammenmaa 84 (1987) 151
Hinode, H., M. Wakihara and M. Taniguchi, Growth of iron niobium sulfide single crystals by chemical transport with iodine 84 (1987) 413
Hodge, A.M., see Pickering 84 (1987) 180
Holt, C., see Harries 84 (1987) 563
Hon, M.H., see Wang 84 (1987) 638
Hukins, D.W.L., see Harries 84 (1987) 563

Imura, T., see Kobayashi 84 (1987) 489
Inada, T., see Fujii 84 (1987) 237
Inoue, N., K. Watanabe, K. Wada and J. Osaka, Time-lag in nucleation of oxide precipitates in silicon due to high temperature preannealing 84 (1987) 21

Ishida, K., see Nakajima 84 (1987) 295
Ishii, M., see Kamon 84 (1987) 126
Ishizawa, N., see Hashimoto 84 (1987) 207
Ito, K., see Sugiyama 84 (1987) 673
Iwanaga, H., see Mochizuki 84 (1987) 1
Iwanaga, H., N. Shibata, A. Tanaka and Y. Masa, Etch pits on the $(511)_A$ and $(\bar{5}\bar{1}\bar{1})_B$ planes in CdTe crystals 84 (1987) 345
Iwasaki, S., see Sugiyama 84 (1987) 673

Jacco, J.C., see Bordui 84 (1987) 403
Jacobsen, C.S., see Bohr 84 (1987) 332
Jasiołek, G., see Gołacki 84 (1987) 455
Johannsen, I., see Bohr 84 (1987) 332
Johansen, T.H., Analysis of the crystal weighing method applied to liquid encapsulated Czochralski growth 84 (1987) 609
Jones, A.C., see Wright 84 (1987) 552
Jones, E.D. and N.M. Stewart, Self-discussion of cadmium in cadmium telluride 84 (1987) 289
Jumas, J.C., see Doukhan 84 (1987) 167

Kamon, K., M. Shimazu, K. Kimura, M. Mihara and M. Ishii, Orientation dependence of GaAs growth in low-pressure OMVPE 84 (1987) 126
Kaneko, T., see Yumoto 84 (1987) 185
Kato, M., see Hashimoto 84 (1987) 207
Khlyunev, N.V., see Bredikhin 84 (1987) 509
Kimura, K., see Kamon 84 (1987) 126
Kimura, T., T. Obokata and T. Fukuda, High speed pulling of GaAs single crystal using the magnetic field applied LEC technique 84 (1987) 394
Kobayashi, S. and T. Muguruma, Effects of an axial magnetic field on solute distribution in Czochralski grown crystals – a further analysis 84 (1987) 559
Kobayashi, T., Y. Nishikawa and T. Imura, Study of the formation mechanism of dislocations during the growth process of aluminium and gallium single crystals from the melt by real time X-ray topography 84 (1987) 489
Kobayashi, T. and N. Uyeda, Structure and defects of a linear chain polymer film; GeO phthalocyanine epitaxially grown on KCl 84 (1987) 589
König, U., see Haspeklo 84 (1987) 196
Korolikhin, V.V., see Bredikhin 84 (1987) 509
Koukitu, A., H. Nakai, T. Suzuki and H. Seki, Thermodynamic analysis of molecular beam epitaxy of II–VI semiconductors 84 (1987) 425
Kragh, F., see Bohr 84 (1987) 332
Krenn, H., see Clemens 84 (1987) 571
Kroes, R.L., see Reiss 84 (1987) 7
Kuramata, A., see Tomiyama 84 (1987) 115

Lall, R.S., see Das 84 (1987) 231
Lambropoulos, J.C., The isotropic assumption during the Czochralski growth of single semiconductors crystals 84 (1987) 349
Langlois, W.E., see Lee, Hyung Mann 84 (1987) 669
Lawrence, M.F., Nguyen Du, R. Philippe and J.-P. Dodelet, Preferential growth of the sphalerite of wurtzite type structure of CdSe thin films by the gas–solid process 84 (1987) 133
Lee, Hyung Mann, Ki-Jun Lee and W.E. Langlois, Effect of co-rotation and counter-rotation on suppression of melt convection in magnetic Czochralski growth 84 (1987) 669
Lee, Ki-Jun, see Lee, Hyung Mann 84 (1987) 669
Lefaucheux, F., see Gits-Léon 84 (1987) 155
Leskelä, M., see Tammenmaa 84 (1987) 151
Leubner, I.H., Crystal formation (nucleation) in the presence of growth restrainers 84 (1987) 496
Leys, M.R., see Van Opdorp 84 (1987) 271
Liu, D.D., see Chen 84 (1987) 303
Lizyakina, V.N., see Bredikhin 84 (1987) 509
Loiacono, G.M., see Bordui 84 (1987) 403
Lousa, A., see Bertran 84 (1987) 483

Ma, M.Y., see Chen 84 (1987) 303
Mach, R., see Hartmann 84 (1987) 199
Madhukar, A., see Thomsen 84 (1987) 79
Madhukar, A., see Thomsen 84 (1987) 98
Majewski, J., see Gołacki 84 (1987) 455
Masa, Y., see Iwanaga 84 (1987) 345
Masumoto, K., see Mochizuki 84 (1987) 1
Matz, H., see Müller 84 (1987) 36
Maurice, V., see Melmed 84 (1987) 123
McCracy, V.R. and V.M. Donnelly, The ultraviolet absorption spectra of selected organometallic compounds used in the chemical vapor deposition of gallium arsenide 84 (1987) 253
McFadden, G.B., R.F. Boisvert and S.R. Coriell, Nonplanar interface morphologies during unidirectional solidification of a binary alloy. II. Three-dimensional computations 84 (1987) 371
Melmed, A.J., V. Maurice, O. Frank and J.H. Block, BCC and FCC forms of Eu epitaxially grown on Re surfaces 84 (1987) 123
Métois, J.J., see Heyraud 84 (1987) 503
Meyer, E., Adiabatic nucleation in large molecule liquids 84 (1987) 533
Mihara, M., see Kamon 84 (1987) 126
Miller, M.J., see Neurgaonkar 84 (1987) 629
Miner, C.J., see Blaauw 84 (1987) 191
Mischgofsky, F.H., see Van Dam 84 (1987) 539
Mizutani, N., see Hashimoto 84 (1987) 207
Mochizuki, K., K. Masumoto and H. Iwanaga, Morphology and photoluminescence (PL) of ZnSe single crystals grown from Se and/or As solvents 84 (1987) 1

Morenza, J.L., see Bertran 84 (1987) 483
Muguruma, T., see Kobayashi 84 (1987) 559
Müller, G., G. Neumann and H. Matz, A two-Raleigh-number model of buoyancy-driven convection in vertical melt growth configurations 84 (1987) 36

Nakai, H., see Koukitu 84 (1987) 425
Nakajima, K., see Tomiyama 84 (1987) 115
Nakajima, M., T. Fujii and K. Ishida, A study of dislocations in In-doped LEC GaAs crystals 84 (1987) 295
Nancollas, G.H., see Arends 84 (1987) 515
Neumann, G., see Müller 84 (1987) 36
Neurgaonkar, R.R., J.R. Oliver and E.T. Wu, Epitaxial growth of ferroelectric films for optoelectronic (SAW) applications 84 (1987) 409
Neurgaonkar, R.R., W.K. Cory, J.R. Oliver, W.W. Clark III, G.L. Wood, M.J. Miller and E.J. Sharp, Growth and ferroelectric properties of tungsten bronze $Ba_{2-x}Sr_xK_{1-y}Na_yNb_5O_{15}$ (BSKNN) single crystals 84 (1987) 629
Nguyen Du, see Lawrence 84 (1987) 133
Nielsen, K.F., see Bohr 84 (1987) 332
Niinistö, L., see Tammenmaa 84 (1987) 151
Nishikawa, Y., see Kobayashi 84 (1987) 489
Nishio, J., see Terashima 84 (1987) 247
Norman, P., see Arber 84 (1987) 145

Obokata, T., see Kimura 84 (1987) 394
Ofner, P., see Clemens 84 (1987) 571
Oliver, J.R., see Neurgaonkar 84 (1987) 409
Oliver, J.R., see Neurgaonkar 84 (1987) 629
Orrell, E.D., see Wright 84 (1987) 552
Osaka, J., see Inoue 84 (1987) 21
Ostrogorsky, A.G., K.H. Yao and A.F. Witt, Infrared absorbance of B_2O_3 at temperatures to 1250 °C 84 (1987) 460
Owczarek, I. and B. Wojciechowski, Nucleation and growth behaviour of KDP from degassed and undegassed aqueous solutions 84 (1987) 329

Panizzieri, R., see Gombia 84 (1987) 621
Paorici, C., see Fornari 84 (1987) 266
Philippe, R., see Lawrence 84 (1987) 133
Philippot, E., see Doukhan 84 (1987) 167
Pickering, C., S. Dixon, D.B. Gasson, D.J. Robbins and A.M. Hodge, Angle-resolved light scattering studies of silicon-on-sapphire 84 (1987) 180
Polychroniadis, E.K., see Toubektsis 84 (1987) 316
Potapenko, S.Yu., see Bredikhin 84 (1987) 509
Pross, E., see Tolksdorf 84 (1987) 323
Pushkarna, A., see Das 84 (1987) 231

Quinlan, K., Equilibrium analysis of the deposition of $In_xGa_{1-x}As$ by the VPE-hydride technique; method to predict the composition of the ternary (E) 84 (1987) 184

Rashkovich, L.N., see Chernov 84 (1987) 389
Reiss, D.A., R.L. Kroes and E.E. Anderson, Growth kinetics of the (001) face of TGS below the ferroelectric transition temperature 84 (1987) 7
Ristolainen, E., see Tammenmaa 84 (1987) 151
Robbins, D.J., see Pickering 84 (1987) 180
Robert, M.C., see Gits-Léon 84 (1987) 155
Rosenberger, F., see Buchan 84 (1987) 359

Salviati, G., see Gombia 84 (1987) 621
Samarasekera, I.V., see Schvezov 84 (1987) 212
Samarasekera, I.V., see Schvezov 84 (1987) 219
Santos, A., see García-Ruiz 84 (1987) 555
Sasse, E., see Haspeklo 84 (1987) 196
Sawada, A., see Sugiyama 84 (1987) 673
Schvezov, C., I.V. Samarasekera and F. Weinberg, Mathematical modelling of the liquid encapsulated Czochralski growth of gallium arsenide. I. Heat flow model 84 (1987) 212
Schvezov, C., I.V. Samarasekera and F. Weinberg, Mathematical modelling of the liquid encapsulated Czochralski growth of gallium arsenide. II. Stress model 84 (1987) 219
Seki, H., see Koukitu 84 (1987) 425
Sharp, E.J., see Neurgaonkar 84 (1987) 629
Shibata, N., see Iwanaga 84 (1987) 345
Shimazu, M., see Kamon 84 (1987) 126
SpringThorpe, A.J., see Blaauw 84 (1987) 431
Stanley, C.R., see Airaksinen 84 (1987) 241
Stephanopoulos, G., see Gevelber 84 (1987) 647
Stewart, N.M., see Jones 84 (1987) 289
Stock, S.R., H. Chen and H.K. Birnbaum, Growth of thin niobium crystals by the strain-anneal method 84 (1987) 419
Stolzenberger, R.A., see Bordui 84 (1987) 403
Su, Y.K., see Chang 84 (1987) 11
Sugiyama, K., A. Sawada, K. Ito, S. Iwasaki and T. Endo, Crystal growth of $CuGaSe_2$ from In solutions 84 (1987) 673
Suzuki, T., see Koukitu 84 (1987) 425

Tammenmaa, M., H. Antson, M. Asplund, L. Hiltunen, M. Leskelä, L. Niinistö and E. Ristolainen, Alkaline earth sulfide thin films grown by atomic layer epitaxy 84 (1987) 151
Tanaka, A., see Iwanaga 84 (1987) 345
Taniguchi, M., see Hinode 84 (1987) 413
Terashima, K., J. Nishio, S. Washizuka and M. Watanabe, Magnetic field effect on residual impurity concentrations for LEC GaAs crystal growth 84 (1987) 247
Testova, N., see Hartmann 84 (1987) 199

Thollet, G., see Vigier 84 (1987) 309
Thomsen, M., S.V. Ghaisas and A. Madhukar, Examination of the nature of lattice matched III–V semiconductor interfaces using computer simulated molecular beam epitaxial growth. I. AC/BC interfaces 84 (1987) 79
Thomsen, M. and A. Madhukar, Examination of the nature of lattice matched III–V semiconductor interfaces using computer simulated molecular beam epitaxial growth. II. $A_xB_{1-x}C$/BC interfaces 84 (1987) 98
Tolksdorf, W., I. Bartels, H. Dammann and E. Pross, Growth of buried garnet channel waveguides by liquid phase epitaxy 84 (1987) 323
Tomiyama, C., A. Kuramata, S. Yamazaki and K. Nakajima, Deposition of InP particles on Si_3N_4 and SiO_2 films by low pressure MOCVD 84 (1987) 115
Toubektsis, S.N. and E.K. Polychroniadis, Growth and structural considerations on single $TlBiSe_2$ crystals 84 (1987) 316
Toudic, Y., see Doukhan 84 (1987) 167
Tsuiki, H., Temperature distribution near the molten zone in a floating zone imaging furnace: effect of absorptivity 84 (1987) 467
Tzeng, H.C., see Chang 84 (1987) 11

Urch, D.S., see Arber 84 (1987) 145
Uyeda, N., see Kobayashi 84 (1987) 589

Van Dam, J.C. and F.H. Mischgofsky, The application of a new, simple interference technique to the determination of growth concentration gradients of the layer perovskite $NH_3(CH_2)_3NH_3CdCl_4$ 84 (1987) 539
Van Landuyt, J., see Zandbergen 84 (1987) 476
Van Opdorp, C. and M.R. Leys, On the factors impairing the compositional transition abruptness in heterojunctions grown by vapour-phase epitaxy 84 (1987) 271
Varela, M., see Bertran 84 (1987) 483
Vassoille, R., see Vigier 84 (1987) 309
Vidal, J., see Gombia 84 (1987) 621
Vigier, G., G. Thollet and R. Vassoille, Cubic and hexagonal ice formation in water–glycerol mixture (50% w/w) 84 (1987) 309

Wada, K., see Inoue 84 (1987) 21
Wakihara, M., see Hinode 84 (1987) 413
Wang, M.C., M.H. Hon and F.S. Yen, Crystallization of β-spodumene in the Li_2O–CaO–Al_2O_3–SiO_2 system 84 (1987) 638
Washizuka, S., see Terashima 84 (1987) 247
Watanabe, K., see Inoue 84 (1987) 21
Watanabe, M., see Terashima 84 (1987) 247
Watanabe, T., see Yumoto 84 (1987) 185
Wei, C.C., see Chang 84 (1987) 11
Weinberg, F., see Schvezov 84 (1987) 212
Weinberg, F., see Schvezov 84 (1987) 219
Weyher, J., see Zandbergen 84 (1987) 476
Wheeler, S.A., see Greene 84 (1987) 259
Whitney, P.S. and C.G. Fonstad, Growth of thin $In_{0.53}Ga_{0.47}As$ layers by liquid phase epitaxy 84 (1987) 676
Williams, A.J., see Wright 84 (1987) 552
Witt, A.F., see Ostrogorsky 84 (1987) 460
Wojciechowski, B., see Owczarek 84 (1987) 329
Wood, G.L., see Neurgaonkar 84 (1987) 629
Wright, P.J., B. Cockayne, A.J. Williams, A.C. Jones and E.D. Orrell, MOCVD layer growth of ZnSe using a new zinc source 84 (1987) 552
Wu, E.T., see Neurgaonkar 84 (1987) 409

Xie, A.Y., see Chen 84 (1987) 303

Yamazaki, S., see Tomiyama 84 (1987) 115
Yao, K.H., see Ostrogorsky 84 (1987) 460
Yen, F.S., see Wang 84 (1987) 638
Yesinowski, J.P., see Arends 84 (1987) 515
Yumoto, H., T. Kaneko, R.R. Hasiguti and T. Watanabe, Morphology and growth mechanism of VLS grown Zn crystals from Zn–Bi monotectic droplets 84 (1987) 185

Zandbergen, H.W., J. Weyher and J. Van Landuyt, High resolution electron microscopy and etching study of twins in GaAs 84 (1987) 476
Zanotti, L., see Fornari 84 (1987) 266
Zawacki, S.J., see Arends 84 (1987) 515
Zecchina, L., see Fornari 84 (1987) 266
Zola, J.J., see Bordui 84 (1987) 403

Journal of Crystal Growth 84 (1987) 693–696
North-Holland, Amsterdam

SUBJECT INDEX

Adsorption 389, 496, 509
Alkaline earth
– sulphides 151
Alloys 371
Aluminum 489
– arsenide 79
– gallium arsenide 98, 271
– organic 271
– phosphate 167
Ammonium
– dihydrogen phosphate 389, 577
Arsenic
– organic 253
Apparatus
– for solution growth
– – by flux method
– – – of potassium titanyl phosphate 403
– – by low temperature method
– – – of organic esters 145
– for thin film growth
– – by gas–solid reaction
– – – of II–VI compounds 133
– – by vapor phase epitaxy
– – – through metalorganic chemical vapor deposition
– – – – of gallium indium arsenide 191
– – – – of heterojunctions 271
– for vapor growth
– – by chemical transport
– – – using steady state source and Knudsen cell arrangement
– – – – of germanium selenide 359
– for miscellaneous purposes
– – determination of growth concentration gradients by interference technique 539
– – high temperature absorbance measurements 460
– – mixing device in gas line for MOCVD 191

Barium
– organic 151
– strontium potassium sodium niobate 629
– sulphide 151
Berlinite, α 167
Boron
– trioxide 460
Boundary layer control 271, 601
Burton–Cabrera–Frank (BCF) theory, 7, 436

Cadmium
– chalcogenides 425
– organic 431
– selenide 133
– sulphide 483
– telluride 289, 345
Calcium
– carbonate 679
– hydroxyapatite 515, 563
– organic 151
– phosphate 563
– sulphide 151
Cellular growth 163, 371, 601
Characterization methods
– by absorption spectroscopy 253
– by atomic absorption spectrometry 413
– by Auger electron spectroscopy 151
– by BET adsorption measurements 515
– by chemical analysis 413, 515, 563
– by differential thermal analysis 515, 638
– by electrical methods 11, 126, 155, 196, 199, 237, 259, 266, 394, 431, 621, 629
– by electroabsorption 259
– by electron diffraction 316, 589, 638
– by electron microscopy 1, 11, 50, 126, 163, 167, 185, 199, 295, 309, 316, 323, 326, 332, 345, 431, 455, 476, 483, 503, 515, 589, 621, 638, 679
– by electron probe microanalysis 11, 326, 455
– by far infrared localized vibrational mode absorption 237
– by ferroelectric properties 629
– by field electron emission microscopy 123
– by Fourier transform infrared 247, 460
– by inductively coupled plasma spectrometry 247
– by magnetic properties 50
– by mass spectrometry 359
– by Mössbauer spectroscopy 50
– by nonlinear optics 403
– by nuclear magnetic resonance 515
– by optical microscopy 50, 115, 126, 155, 295, 345, 389, 403, 413, 455, 476, 552
– by optical properties 629
– by photoluminescence 1, 98, 191, 199, 673
– by Raman spectroscopy 577
– by reflection high energy electron diffraction 79, 199, 241
– by SAW velocity 409
– by scattering techniques 180
– by secondary ion mass spectrometry 237, 259, 431
– by spark source analysis 419
– by superconductivity 332
– by thermogravimetry 413
– by transmission spectroscopy 167, 259, 394, 515, 563
– by X-ray techniques 11, 50, 133, 145, 151, 196, 207, 295, 309,

316, 326, 359, 409, 413, 419, 431, 455, 483, 489, 552, 563, 571, 621, 629, 638, 673, 679
Computer simulation 79, 98, 212, 219, 467, 669
Constitutional supercooling 163, 601
Convection 36, 163, 196, 247, 335, 509, 598
Copper
– gallium diselenide 673

Dendritic growth 601
Diffusional control 155, 271, 509, 555, 601
Dislocations 167, 212, 219, 237, 266, 295, 316, 349, 389, 419, 476, 489, 589
Dissolution 167, 436, 539
Distribution coefficient 247, 399, 559
Dopants 1, 199, 241, 295, 409, 431, 483, 629, 676

Electrical double layer theory 303
Etching
– chemical 1, 11, 126, 259, 266, 295, 323, 326, 345, 394, 419, 431, 476, 552
Europium 123
Eutectic growth 629

Finite element method 349

Gallium 489
– antimonide 349
– arsenide 126, 212, 219, 237, 241, 247, 253, 266, 271, 349, 476, 598, 609, 647
– indium arsenide 191
– organic 126, 191, 196, 253, 271
Garnets 323, 399
Germanium
– oxide phthalocyanine polymer $(C_{32}N_8H_{16}GeO)_n$ 589
– selenide 359

Heat flow control 57, 212, 460, 467, 598, 647
Heterojunction 271
Hydrodynamics 36

Ice 309
Impurity 167, 237, 247, 389, 496, 509, 629
Indium
– gallium arsenide 163, 196, 676
– gallium arsenide phosphide 259
– organic 115, 191, 196, 431
– phosphide 115, 241, 349, 431
Intercalation compounds 413
Interface 57, 79, 98, 185, 271, 295, 371, 389, 489, 601, 609, 647
Iron
– niobium sulphide 413

Kinetics
– of dissolution 436, 515
– of growth 7, 79, 98, 126, 151, 199, 241, 303, 309, 389, 496, 509, 515, 555, 571, 601, 676, 679
– of interface control 79, 98, 389, 601, 609
– of nucleation 21, 231, 309, 601

Lanthanum
– calcium manganese oxide 207
– strontium manganese oxide 207
Lattice mismatch 79, 98, 191, 196
Layer uniformity 191, 196
Lead
– chromate 231
– germanide telluride 571
– telluride 455
Lithium
– iodate 303
– oxide–calcium oxide–alumina–silica system 638
– niobate 409
– tantalate 409

Magnetite 50
Melt growth technique
– by Bridgman–Stockbarger method
– – of aluminum 489
– – of cadmium telluride 345
– – of gallium 489
– – of gallium arsenide 476
– – of lead telluride 455
– – of thallium bismuth selenide 316
– – of zinc selenide 11
– by Czochralski method
– – of barium strontium potassium sodium niobate 629
– – of boron trioxide 460
– – of gallium arsenide 212, 219, 237, 247, 266, 295, 394, 598, 609, 647
– – of silicon 21, 57, 349
– – of III–V compounds 349
– – mathematical modeling of 212, 219, 598, 609
– – theory of 559, 647, 669
– by floating zone method
– – of lanthanum calcium manganese oxide 207
– – of lanthanum strontium manganese oxide 207
– – temperature distribution of, near melt 467
– theory of 36
Molecular adsorption theory 303
Monte Carlo method 436
Morphological stability 371, 601, 679
Morphology of growth 1, 11, 50, 126, 133, 185, 303, 332, 431, 483, 489, 496, 503, 552, 601, 621, 679

Niobium 419
Nucleation 21, 115, 123, 309, 329, 496, 533, 589, 679
Numbers
– Grashof 509, 598
– Prandtl 36, 509
– Rayleigh 36
– Stranski–Krastanov 123

Optoelectronics 629
Organic crystals 7, 145, 539, 589

Perfection of crystals 1, 11, 21, 50, 167, 196, 266, 295, 349, 394, 399, 403, 419, 433, 455, 489, 577

Perovskite 539
Phase diagrams 185, 409, 629, 673
Phenomenological theory 21, 332, 389
Potassium
– dihydrogen phosphate 329, 389, 509, 555, 577
– titanyl phosphate 403
Propylene diammonium cadmium tetrachloride 539

Quantum wells/size effects 79

Self-diffusion
– of cadmium 289
Silicon 21, 180, 335, 349
– polycrystalline 621
Silver
– chloride 496
Size distribution 50, 496
Sodium
– chloride 155, 503
– dihydrogen phosphate 577
Solid growth technique
– by polymorphic transformation
– – of lithium oxide–calcium oxide–alumina–silica system 638
– by recrystallization
– – of polycrystalline silicon 621
– by strain anneal
– – of niobium 419
Solid solution 629, 673
Solution growth technique
– by flux method
– – of copper gallium diselenide 673
– – of potassium titanyl phosphate 403
– – of zinc selenide 1
– by gel method
– – of lead chromate 231
– – of potassium dihydrogen phosphate 555
– – of silver chloride 496
– by hydrothermal method
– – of α-berlinite (aluminum phosphate) 167
– – of magnetite 50
– by low temperature method
– – of calcium carbonate 679
– – of calcium hydroxyapatite 515, 563
– – of dihydrogen orthophosphates 577
– – of layer perovskite 539
– – of lithium iodate 303
– – of organic esters 145
– – of potassium dihydrogen phosphate 329, 389, 509
– – of propylene diammonium cadmium tetrachloride 539
– – of triglycine sulphate 7
– – theory of 389, 577
– theory of 7
Statistical mechanics, molecular theory 577
Stefan problem or moving boundary problem 57, 371, 601
Step 335
Strain 212, 219, 349
Strontium
– organic 151
– sulphide 151
Supercooling, supersaturation 7, 163, 329, 509, 533, 539, 629
Superlattices 259, 571
Superstructure 316
Surface processes, theory 577
Surface structure 503, 515

Thallium
– bismuth selenide 316
Thermodynamics 115, 167, 199, 231, 241, 247, 359, 413, 425, 533, 598
Thin film growth
– by atomic layer epitaxy
– – of alkaline earth sulphides 151
– by gas-solid reaction
– – of II–VI compounds 133
– by liquid phase epitaxy
– – of indium gallium arsenide 163, 676
– – of indium gallium arsenide phosphide 259
– – of lithium niobate 409
– – of lithium tantalate 409
– – of tin 326
– – of yttrium aluminum garnet, substituted by scandium 399
– – of yttrium iron garnet, substituted by bismuth and gallium 323
– by molecular beam epitaxy
– – of aluminum arsenide 79
– – of aluminum gallium arsenide 98
– – of gallium arsenide 241
– – of indium phosphide 241
– – theory of 79, 425
– by vapor phase epitaxy
– – through chemical vapor transport
– – – of zinc selenide 199
– – – of zinc sulphide 199
– – through evaporation and condensation
– – – of cadmium sulphide 483
– – – of europium 123
– – – of germanium oxide phthalocyanine polymer 589
– – through hot wall epitaxy
– – – of lead germanide telluride 571
– – through metalorganic chemical vapor deposition
– – – of aluminum gallium arsenide 271
– – – of gallium arsenide 126, 253, 271
– – – of gallium indium arsenide 191
– – – of indium gallium arsenide 196
– – – of indium phosphide 115, 431
– – – of zinc selenide 552
Three–five (III–V) compounds 79, 98, 349
Tin 326
Triglycine sulphate 7
Tungsten bronze 629
Twinning 167, 180, 345, 476
Two–six (II–VI) compounds 133, 425

Vapor growth technique

– by chemical transport
– – of germanium selenide 359
– – of iron niobium sulphide 413
– by evaporation and condensation
– – of sodium chloride 503
Vapor–liquid–solid growth
– of zinc 185

Waveguide 323

Yttrium
– aluminum garnet, substituted by scandium 399
– barium copper oxide system 332
– iron garnet, substituted by bismuth and gallium 323

Zinc 185
– chalcogenides 425
– selenide 1, 11, 199, 552
– sulphide 199